
HZM6.8ZWA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-613 (Z)

Rev 0

April 1, 1998

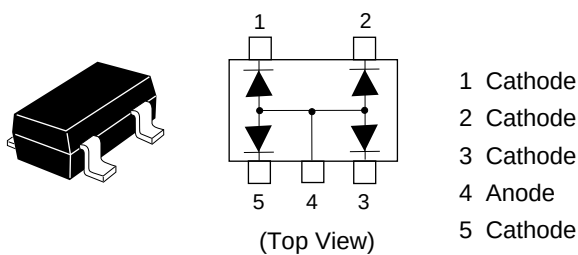
Features

- HZM6.8ZWA has two devices, and can absorb external + and -surge.
- Low capacitance ($C=25\text{pF}$ max) and can protect ESD of signal line.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.8ZWA	68Z	MPAK

Outline



HZM6.8ZWA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd ^{*1}	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Two device total, See Fig.2.

Electrical Characteristics (Ta = 25°C) ^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _Z	6.47	—	7.00	V	I _Z = 5 mA, 40ms pulse
Reverse current	I _R	—	—	2	μA	V _R = 3.5V
Capacitance	C	—	—	25	pF	V _R = 0V, f = 1 MHz
Dynamic resistance	r _d	—	—	30	Ω	I _Z = 5 mA
ESD-Capability ^{*2}	—	20	—	—	kV	C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes 1. Per one device.

2. Failure criterion ; IR > 2 μA at VR = 3.5V.

Main Characteristic

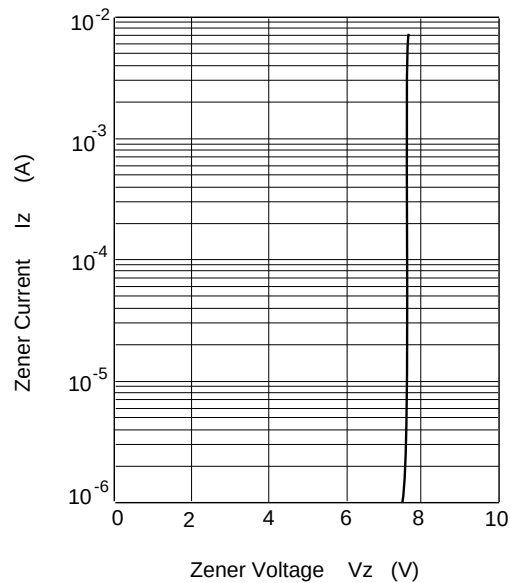


Fig.1 Zener current Vs. Zener voltage

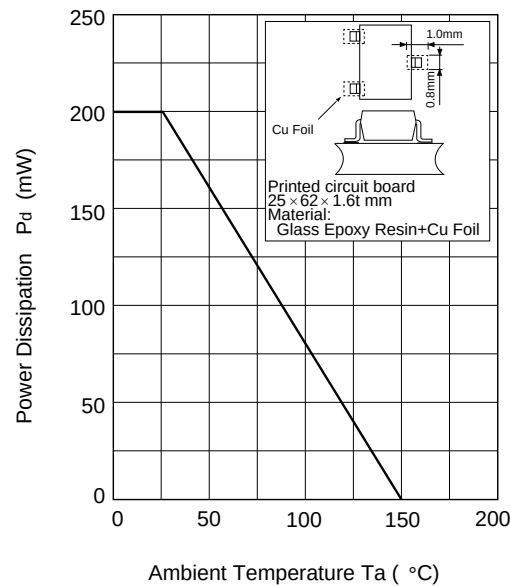


Fig.2 Power Dissipation Vs. Ambient Temperature

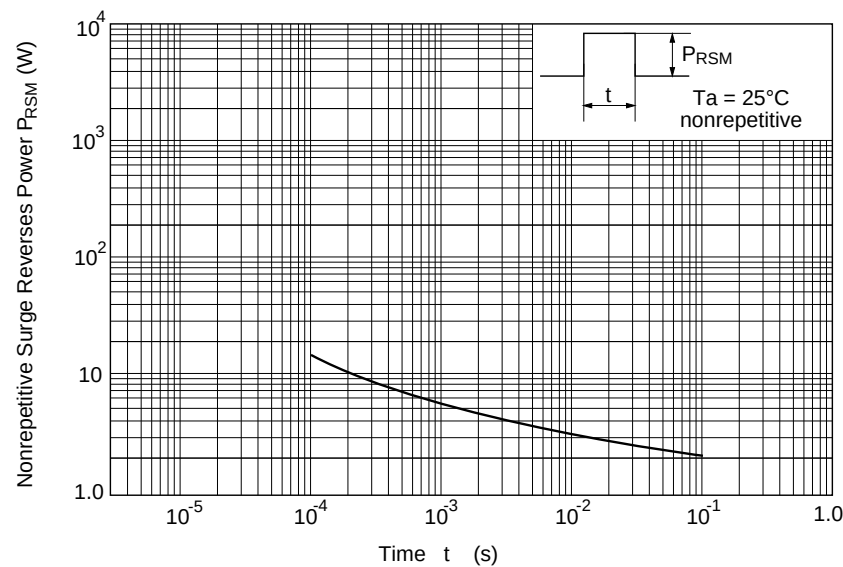


Fig.3 Surge Reverse Power Ratings

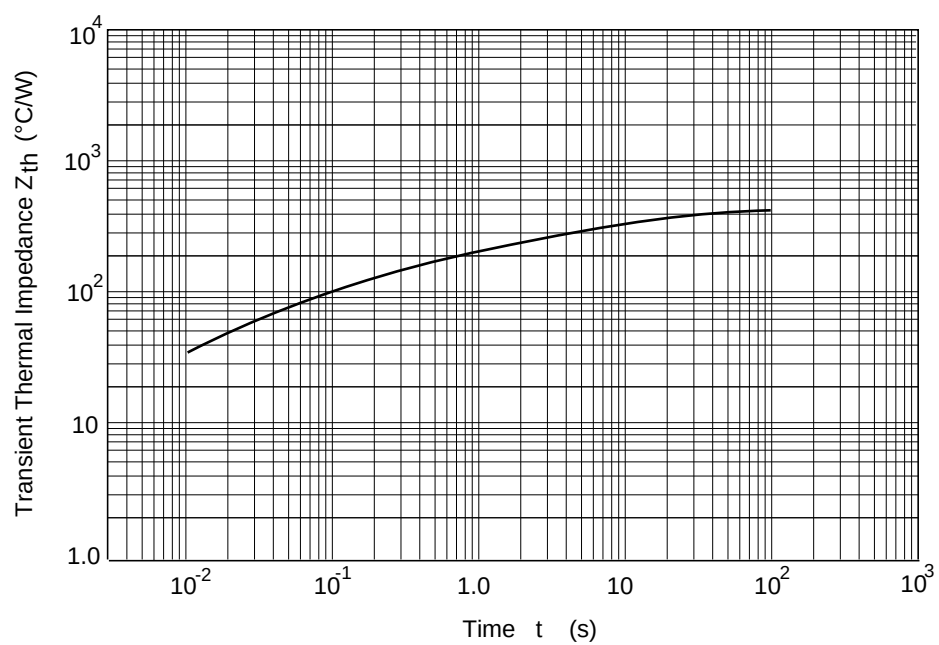
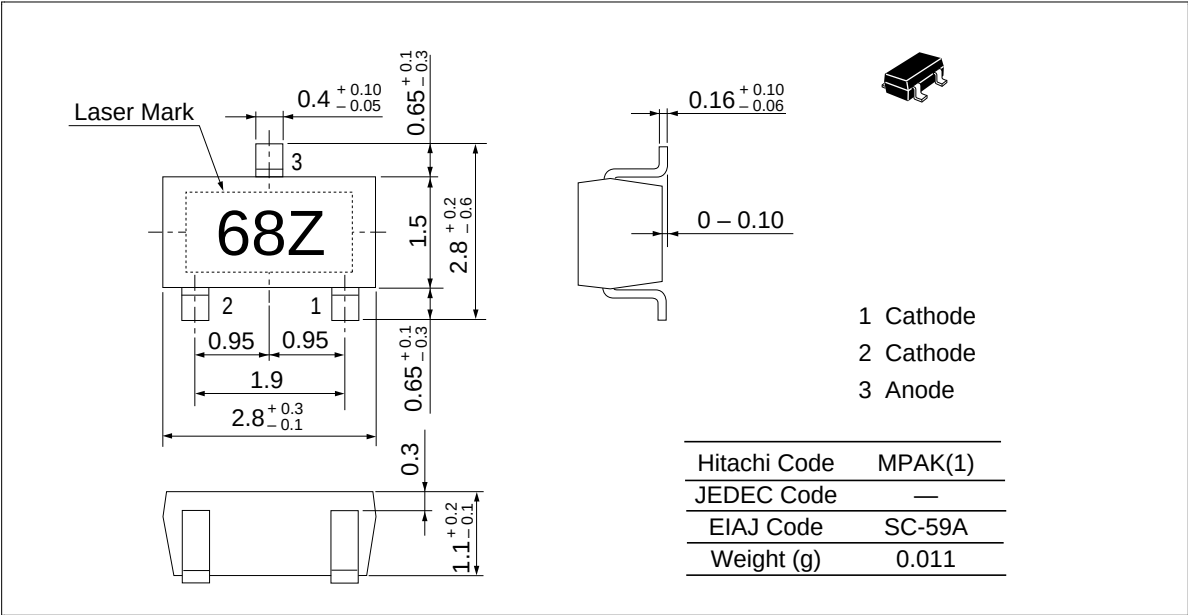
Main Characteristic

Fig.4 Transient Thermal Impedance

Package Dimensions (Unit: mm)



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1897
U S A
Tel: 800-285-1601
Fax: 303-297-0447

Hitachi Europe GmbH
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

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